TE SEM-VICBSGS/ETRX/Nov 17 Bosic VLSI Design

b Later up in CMOS

d ESD protection.

c Decoder in Memory Structure.

Q.P. Code :10652

[Marks:80]

		Please check whether you have got the right question paper.	
	N.B:	1. Question No. 1 is compulsory.	3,70
		2. Attempt any three questions from remaining five questions.	9.00
		3. Assume suitable data where required.	500
		4. Figures to the right indicate full marks.	
	(Salva anu 4)		S. T.
-	(Solve any 4)	& CMOS technology in VLSI design.	05
		e following function using Static CMOS.	05
	b) implement the	$Y = \overline{(A + B)(C + D)}$	US
	cl Implement half	f adder circuit using static CMOS.	05
	The state of the s	4. NAND based ROM array.	05
	The state of the s	ance of Low power design.	05
	ej explain import	ance of Low power design.	
2	a] What are the d	lifferent MOSFET Models? Give importance of MOSFET capacitances related to MOSFET's	10
	performance.		
		r characteristics for CMOS Inverter showing different regions. What is the effect of variation	10
	in W/L ratio?		
3	a] Draw 6T SRAM	cell and explain it's read & write operation.	10
	b] Explain Scheme	e for multiplication of 110*100	10
4	al Explain various	techniques of clock generation & clock distribution.	10
		multiplexer using NMOS pass transistor logic.	10
	al Draw D Ellis Ele	the using CMOS and available the worlding	10
9		p using CMOS and explain the working.	
	Draw CLA (carr	ry lookahead adder) carry chain using Static CMOS logic.	10
5	Write Short notes	son.	20
	al Interconnect S	caling Selection of the control of t	

[Time: 3 Hours]

Q. P. Code: 25078

Time:-3 Hours Marks:-80 SEB (1) Question No. 1 is compulsory Attempt any 3 questions from remaining questions (3) Figures to the right indicate full marks. 1 a. Solve using Booth's algorithm Multiplicand M=+7 and Multiplier Q=+3. b. Write microinstructions for the instruction ADD R3, R2, R1. c. Explain SIMD computer organization. d. Explain various types of memories Q.2 a. What is cache coherency? Explain various methods to achieve it. 10 b. Explain various pipelining hazards and solutions for the same. 10 Q.3 a. Explain micro-programmed control unit with a neat diagram. 10 b. Explain briefly various cache mapping techniques 10 Q.4 a .What is virtual memory? Explain how paging is implemented in virtual memory. 10 b. Find page fault for the following string using FIFO, LRU and LFU page 10 Replacement policies for the page address stream 2 1 2 3 1 5 4 2 1 5. Consider page frame size n=3. Q.5 a. Explain various DMA transfer modes. 10 b. Explain Flynn's classification. 10 Q.6 a. Explain various bus arbitration techniques. 10 b. Explain the register structure of IA-32 family. 10

ronics/Sem-VI-(CBSGIS)/Power Electronics-I/Dec-2017

Q. P. Code: 13681

REVISED COURSE

(3 Hours)	Total Marks: 80
1) Question No. 1 is compulsory.	
2) Attempt any three questions out of the remaining five questions.	

3) Figures to the right indicate full marks.

4) Assume suitable data wherever required but justify the same.

Compare the various triggering methods of thyristors.	20
What is the need of freewheeling diode in rectifiers? Explain with an example.	
Draw and explain VI characteristic of TRIAC.	
Explain the commutation techniques for SCR. Draw any one, forced commutation circuit.	
e) Explain various control strategies for DC-DC converter.	
Q2 a) Draw and explain single phase fully controlled converter with RL load .Draw load current, load	
voltage input voltage and gating signal for $\alpha = 60^{\circ}$.	10
b) Explain the working of three phase bridge inverter in 180 degree conduction mode with circuit diagram	
and waveforms.	10
\mathbb{Q}^3 a) A single phase full bridge inverter has a resistive load of $10~\Omega$ and dc input voltage of 48 V.	10
Calculate: i) RMS output voltage V rms.	
ii) RMS output voltage at fundamental frequency V(01) _{rms} iii) Total Harmonic Distortion (THD) iv) Average and peak current of each thyristor	10
b) Explain working principle of single phase cyclo converter with circuit diagram and waveforms.	10
Q4. a) A single phase fully controlled converter is operated from 230V, 50Hz ac supply. The load resistance	
is 10 Ohms. The average output voltage is 10% of max possible average output voltage.	10
Calculate:- i) Firing angle	
ii) RMS and Average output current	
iii) Efficiency	
iv) Displacement Factor (DF)	
b) Draw and explain the working of 3Φ fully controlled rectifier with neat circuit diagram and	10
Waveforms.	
Q5. a) Draw and explain AC voltage control circuit using DIAC and TRIAC .Draw the waveforms with-	10
$\alpha = 45^{\circ}$	
b) Draw and explain Boost converter with waveforms. Also derive the expression for output voltage.	10
a) Compare IGBT, MOSFET and GTO. b) Protection circuits for SCR. c) Driver circuits for power transistors.	20

d) Voltage control of inverters using PWM techniques.

ectronics/Sem III-(CBSUIS)/Digital Signal Processing and Processors/Dec-2017

Q.P.Code: 016379

(3 Hours)

[Total Marks: 80]

NB:

1) Question No. ONE is compulsory.

- 2) Out of remaining questions, attempt any THREE questions.
- 3) In all FOUR questions to be attempted.
- 4) All questions carry equal marks.
- 5) Answer to each new question to be started on a fresh page.
- 6) Figures in brackets on the right hand side indicate full marks.
- 7) Assume Suitable data if necessary

Q1. Attempt any four

(20 marks)

- a) Differentiate between Butterworth and Chebyshev filters.
- b) Explain frequency wrapping effect in designing IIR filter.
- c) State the relationship between DFS, DFT and Z transform.
- d) What is DTFS. Find DTFS of $x(n)=\{0,1,2,3\}$ with period N=4.
- e) Compare DSP processor and microprocessor.
- - b) Write down design steps for FIR filter using window techniques. Compare windows. (10 marks)
- Q3. a) Design analog Butterworth filter that has -2 dB passband attenuation of 20 rad/sec and at least -10 dB stopband attenuation at 30 rad/sec. (10 marks)
 - b) Compute the circular convolution of the sequence using DFT and IDFT, $\times 1(n) = \{1,2,0\}$ and $\times 2(n) = \{2,2,1,1\}$ (10 marks)
- Q4. a) Given H(s)= [1/(s+1)(s+3)], T=2 seconds. Design digital IIR filter using BLT method. Explain advantages of BLT over IIM method. (10 marks)
 - b) Design 6th order linear phase LPF with cut off frequency π/2 using Blackman window. (10 marks)
- Q5, a) Design Butterworth LPF to meet following specifications

Passband gain is 0.89

Passband frequency edge 30Hz

Attenuation 0.20

Stopband edge 75Hz

(10 marks)

b) Design the symmetric FIR LPF where desired frequency response is given as

$$Hd(w) = \begin{cases} e^{(-jwt)} & \text{for } |w| \le w_c \text{ otherwise} \\ 0 & \end{cases}$$

(10 marks)

Q6. Write short note on following (Any two)

(20 marks)

- a) Gibb's Phenomenon
- b) Application of DSP in speech and Radar processing
- c) Limit cycle Oscillations

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